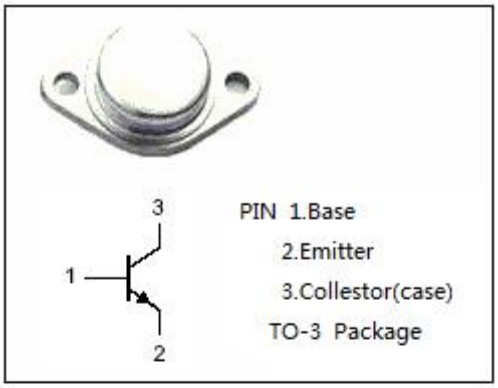
isc Silicon NPN Power Transistors 2SD583

DESCRIPTION

- High Current Capability
- Excellent Safe Operating Area
- High DC current Gain
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

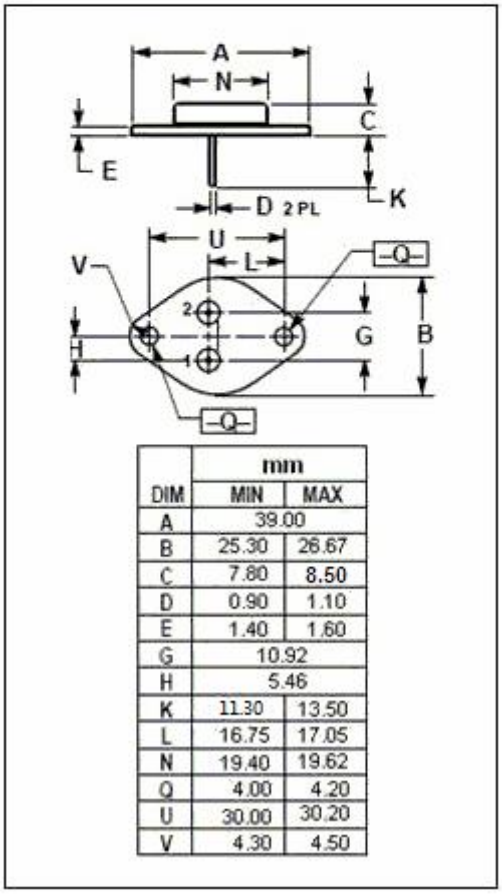


APPLICATIONS

- Designed for high power audio, disk head positioners and other linear applications

ABSOLUTE MAXIMUM RATINGS(T_C=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	250	V
V_{CEO}	Collector-Emitter Voltage	250	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	15	A
I_{CM}	Collector Current-Peak	25	A
I_B	Base Current-Continuous	5	A
P_D	Total Power Dissipation @T_C=25℃	150	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-65~150	℃



DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

isc Silicon NPN Power Transistors 2SD583

ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 50mA ;I_B= 0	250		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= 8A; I_B= 0.8A		1.4	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= 15A; I_B= 3A		4.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= 8A ; V_{CE}= 4V		2.2	V
I_{CEO}	Collector Cutoff Current	V_{CE}= 250V; I_B= 0		0.5	mA
I_{CBO}	Collector Cutoff Current	V_{CB}= 250V; I_E= 0		0.1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C=0		0.1	mA
h_{FE-1}	DC Current Gain	I_C= 2A ; V_{CE}= 5V	60	200	
h_{FE-2}	DC Current Gain	I_C= 8A ; V_{CE}= 5V	30		
f_T	Current-Gain—Bandwidth Product	I_C= 1A ; V_{CE}= 10V; f_{test}= 1.0MHz	4		MHz